

MA3G751, MA3G751A

Silicon epitaxial planar type (cathode common)

For switching power supply

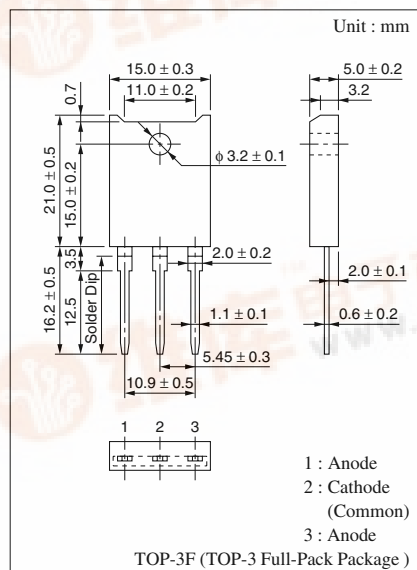
■ Features

- Forward current (average) $I_{F(AV)}$: 20 A type
- High reliability caused by sealed in the TOP-3F (Full-pack package)
- Cathode common dual type
- Low forward rise voltage V_F

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	MA3G751	V_{RRM} 40	V
	MA3G751A	45	
Average forward current	$I_{F(AV)}$	20	A
Non-repetitive peak forward surge current*	I_{FSM}	150	A
Junction temperature	T_j	-40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

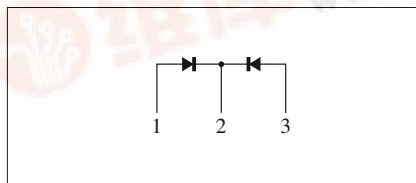
Note) * : Half sine-wave: 10 ms/cycle



Marking Symbol

- MA3G751 : MA3G751
- MA3G751A : MA3G751A

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	MA3G751	I_R $V_R = 40\text{ V}$			5	mA
	MA3G751A	$V_R = 45\text{ V}$			5	
Forward voltage (DC)	V_F	$I_F = 10\text{ A}$			0.55	V
Thermal resistance	$R_{th(j-c)}$	Direct current (between junction and case)			1.5	$^\circ\text{C/W}$

Note) Rated input/output frequency: 100 MHz

